# Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

Diodes Incorporated
DMC31D5UDJ-7B

For any questions, you can email us directly:
sales@integrated-circuit.com

DIODES INCORPORATED

Lead-free Green

**DMC31D5UDJ**

**COMPLEMENTARY PAIR ENHANCEMENT MODE MOSFET**

NEW PRODUCT

## Product Summary

| Device | $V_{(BR)DSS}$ | $R_{DS(ON)}$ max | $I_D$ max $T_A$ = +25°C |
|---|---|---|---|
| Q1 | 30V | 1.5Ω @ $V_{GS}$ = 4.5V | 0.22A |
| | | 2.0Ω @ $V_{GS}$ = 2.5V | |
| | | 3.0Ω @ $V_{GS}$ = 1.8V | |
| | | 4.5Ω @ $V_{GS}$ = 1.5V | |
| Q2 | -30V | 5Ω @ $V_{GS}$ = -4.5V | -0.2A |
| | | 6Ω @ $V_{GS}$ = -2.5V | |
| | | 7Ω @ $V_{GS}$ = -1.8V | |
| | | 10Ω @ $V_{GS}$ = -1.5V | |

## Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

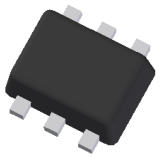
## Features and Benefits

- Low On-Resistance
- Very low Gate Threshold Voltage, 1.0V max
- Low Input Capacitance
- Fast Switching Speed
- Ultra-Small Surface Mount Package 1mm x 1mm
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 standards for High Reliability**

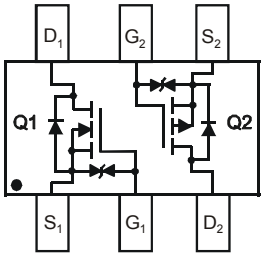
## Mechanical Data

- Case: SOT963
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.027 grams (approximate)


SOT963



Top View



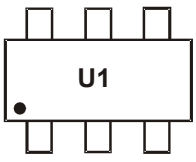

Top View
Schematic and
Transistor Diagram

## Ordering Information (Note 4)

| Part Number | Case | Packaging |
|---|---|---|
| DMC31D5UDJ-7 | SOT963 | 10K/Tape & Reel |
| DMC31D5UDJ-7B | SOT963 | 10K/Tape & Reel |

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html. The options -7 and -7B stand for different taping orientations.

## Marking Information




U1 = Product Type Marking Code

NEW PRODUCT

## Maximum Ratings Q1 N-CHANNEL (@$T_A$ = +25°C, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Units |
|---|---|---|---|---|---|
| Drain-Source Voltage | | | $V_{DSS}$ | 30 | V |
| Gate-Source Voltage | | | $V_{GSS}$ | ±12 | V |
| Continuous Drain Current (Note 5) $V_{GS}$ = 4.5V | Steady State | $T_A$ = +25°C<br>$T_A$ = +70°C | $I_D$ | 220<br>160 | mA |
| Maximum Continuous Body Diode Forward Current (Note 6) | | | $I_S$ | 200 | mA |
| Pulsed Drain Current (Note 6) | | | $I_{DM}$ | 600 | mA |

## Maximum Ratings Q2 P-CHANNEL (@$T_A$ = +25°C, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Units |
|---|---|---|---|---|---|
| Drain-Source Voltage | | | $V_{DSS}$ | -30 | V |
| Gate-Source Voltage | | | $V_{GSS}$ | ±12 | V |
| Continuous Drain Current (Note 5) $V_{GS}$ = -4.5V | Steady State | $T_A$ = +25°C<br>$T_A$ = +70°C | $I_D$ | -200<br>-140 | mA |
| Maximum Continuous Body Diode Forward Current (Note 6) | | | $I_S$ | -200 | mA |
| Pulsed Drain Current (Note 6) | | | $I_{DM}$ | -600 | mA |

## Thermal Characteristics (@$T_A$ = +25°C, unless otherwise specified.)

| Characteristic | | Symbol | Value | Units |
|---|---|---|---|---|
| Total Power Dissipation (Note 5) | | $P_D$ | 350 | mW |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State | $R_{\theta JA}$ | 361 | °C/W |
| Operating and Storage Temperature Range | | $T_J$, $T_{STG}$ | -55 to +150 | °C |

## Electrical Characteristics Q1 N-CHANNEL (@$T_A$ = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS (Note 7)** | | | | | | |
| Drain-Source Breakdown Voltage | $BV_{DSS}$ | 30 | — | — | V | $V_{GS}$ = 0V, $I_D$ = 250μA |
| Zero Gate Voltage Drain Current @$T_C$ = +25°C | $I_{DSS}$ | — | — | 100 | nA | $V_{DS}$ = 24V, $V_{GS}$ = 0V |
| Gate-Source Leakage | $I_{GSS}$ | — | — | ±10 | μA | $V_{GS}$ = ±10V, $V_{DS}$ = 0V |
| **ON CHARACTERISTICS (Note 7)** | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | 0.4 | — | 1.0 | V | $V_{DS}$ = $V_{GS}$, $I_D$ = 250μA |
| Static Drain-Source On-Resistance | $R_{DS(ON)}$ | — | 0.9 | 1.5 | Ω | $V_{GS}$ = 4.5V, $I_D$ = 100mA |
| | | — | 1.0 | 2.0 | | $V_{GS}$ = 2.5V, $I_D$ = 50mA |
| | | — | 1.2 | 3.0 | | $V_{GS}$ = 1.8V, $I_D$ = 20mA |
| | | — | 1.4 | 4.5 | | $V_{GS}$ = 1.5V, $I_D$ = 10mA |
| | | — | 2.3 | — | | $V_{GS}$ = 1.2V, $I_D$ = 1mA |
| Diode Forward Voltage | $V_{SD}$ | — | 0.6 | 1.0 | V | $V_{GS}$ = 0V, $I_S$ = 10mA |
| **DYNAMIC CHARACTERISTICS (Note 8)** | | | | | | |
| Input Capacitance | $C_{iss}$ | — | 22.6 | — | pF | $V_{DS}$ = 15V, $V_{GS}$ = 0V, f = 1.0MHz |
| Output Capacitance | $C_{oss}$ | — | 2.68 | — | pF | |
| Reverse Transfer Capacitance | $C_{rss}$ | — | 1.8 | — | pF | |
| Total Gate Charge | $Q_g$ | — | 0.38 | — | nC | $V_{GS}$ = 4.5V, $V_{DS}$ = 15V, $I_D$ = 200mA |
| Gate-Source Charge | $Q_{gs}$ | — | 0.05 | — | nC | |
| Gate-Drain Charge | $Q_{gd}$ | — | 0.07 | — | nC | |
| Turn-On Delay Time | $t_{D(on)}$ | — | 3.2 | — | ns | $V_{DD}$ = 15V, $V_{GS}$ = 4.5V, $R_G$ = 2Ω, $I_D$ = 200mA |
| Turn-On Rise Time | $t_r$ | — | 2.2 | — | ns | |
| Turn-Off Delay Time | $t_{D(off)}$ | — | 21 | — | ns | |
| Turn-Off Fall Time | $t_f$ | — | 7.5 | — | ns | |

NEW PRODUCT

## Electrical Characteristics Q2 P-CHANNEL (@$T_A$ = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS (Note 7)** | | | | | | |
| Drain-Source Breakdown Voltage | $BV_{DSS}$ | -30 | — | — | V | $V_{GS}$ = 0V, $I_D$ = -250μA |
| Zero Gate Voltage Drain Current @$T_C$ = +25°C | $I_{DSS}$ | — | — | 100 | nA | $V_{DS}$ = -24V, $V_{GS}$ = 0V |
| Gate-Source Leakage | $I_{GSS}$ | — | — | ±10 | μA | $V_{GS}$ = ±10V, $V_{DS}$ = 0V |
| **ON CHARACTERISTICS (Note 7)** | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | -0.4 | — | -1.0 | V | $V_{DS}$ = $V_{GS}$, $I_D$ = -250μA |
| Static Drain-Source On-Resistance | $R_{DS(ON)}$ | — | 2.0 | 5 | Ω | $V_{GS}$ = -4.5V, $I_D$ = -100mA |
| | | — | 2.5 | 6 | | $V_{GS}$ = -2.5V, $I_D$ = -50mA |
| | | — | 3.0 | 7 | | $V_{GS}$ = -1.8V, $I_D$ = -20mA |
| | | — | 3.4 | 10 | | $V_{GS}$ = -1.5V, $I_D$ = -10mA |
| | | — | 5.1 | — | | $V_{GS}$ = -1.2V, $I_D$ = -1mA |
| Diode Forward Voltage | $V_{SD}$ | — | -0.6 | -1.0 | V | $V_{GS}$ = 0V, $I_S$ = -10mA |
| **DYNAMIC CHARACTERISTICS (Note 8)** | | | | | | |
| Input Capacitance | $C_{iss}$ | — | 21.8 | — | pF | $V_{DS}$ = -15V, $V_{GS}$ = 0V, f = 1.0MHz |
| Output Capacitance | $C_{oss}$ | — | 2.82 | — | pF | |
| Reverse Transfer Capacitance | $C_{rss}$ | — | 1.66 | — | pF | |
| Total Gate Charge | $Q_g$ | — | 0.35 | — | nC | $V_{GS}$ = -4.5V, $V_{DS}$ =- 15V, $I_D$ = -200mA |
| Gate-Source Charge | $Q_{gs}$ | — | 0.05 | — | nC | |
| Gate-Drain Charge | $Q_{gd}$ | — | 0.10 | — | nC | |
| Turn-On Delay Time | $t_{D(on)}$ | — | 3.5 | — | ns | $V_{DD}$ = -15V, $V_{GS}$ = -4.5V, $R_G$ = 2Ω, $I_D$ = -200mA |
| Turn-On Rise Time | $t_r$ | — | 5.2 | — | ns | |
| Turn-Off Delay Time | $t_{D(off)}$ | — | 18.8 | — | ns | |
| Turn-Off Fall Time | $t_f$ | — | 8.7 | — | ns | |

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
6. Device mounted on minimum recommended pad layout test board, 10μs pulse duty cycle = 1%.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

NEW PRODUCT

## N-CHANNEL

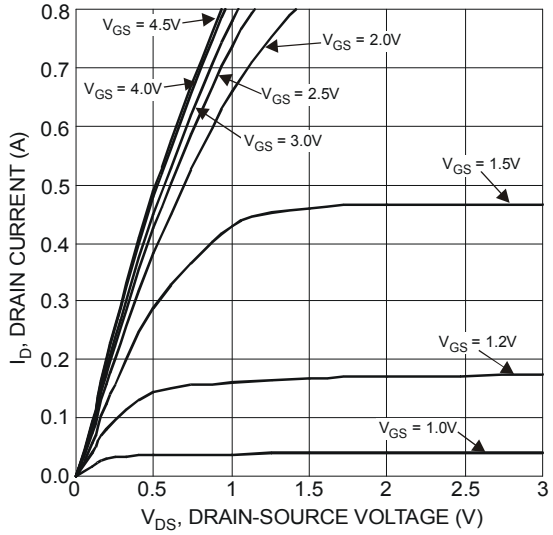



Figure 1 Typical Output Characteristics

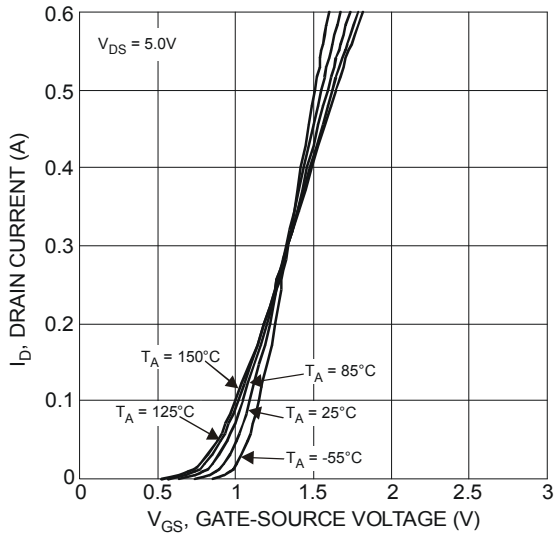



Figure 2 Typical Transfer Characteristics

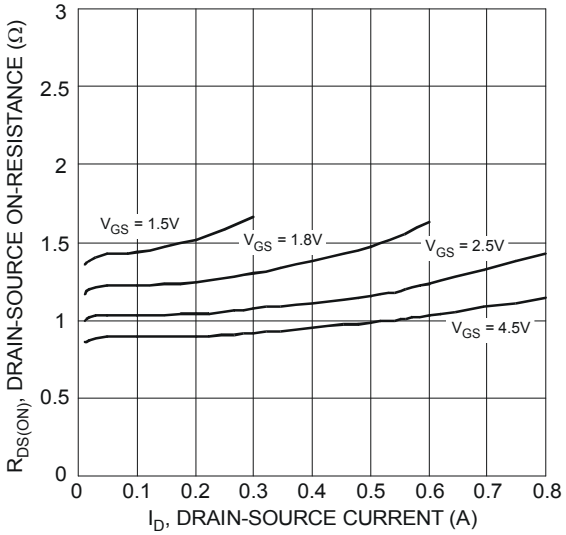



Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

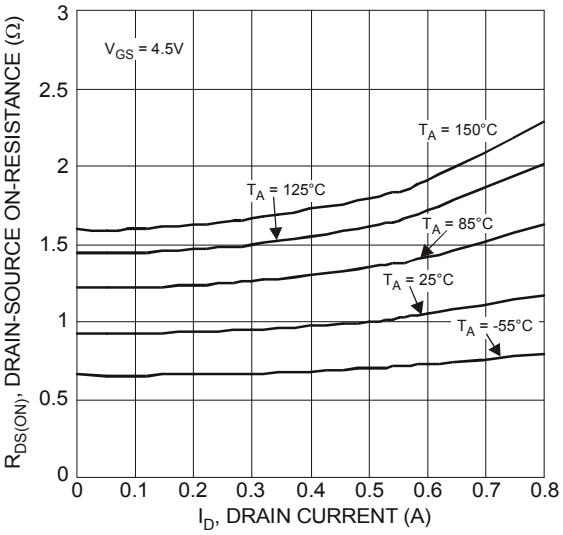



Figure 4 Typical On-Resistance vs. Drain Current and Temperature

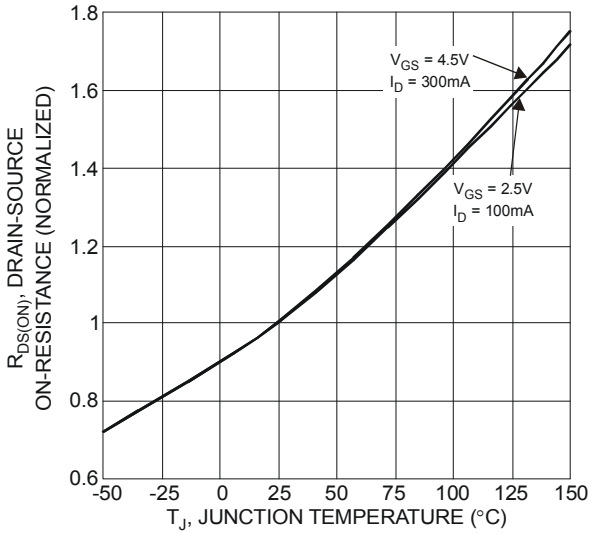



Figure 5 On-Resistance Variation with Temperature

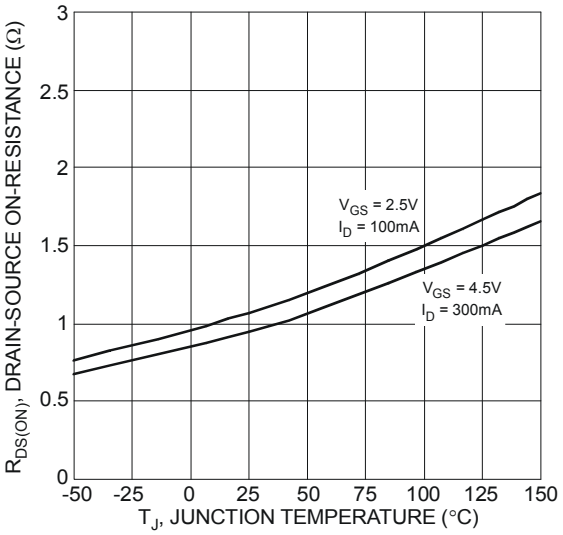



Figure 6 On-Resistance Variation with Temperature

NEW PRODUCT

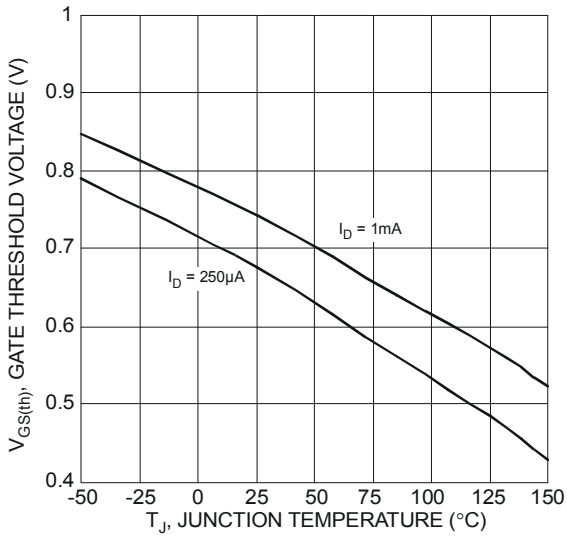



Figure 7 Gate Threshold Variation vs. Ambient Temperature

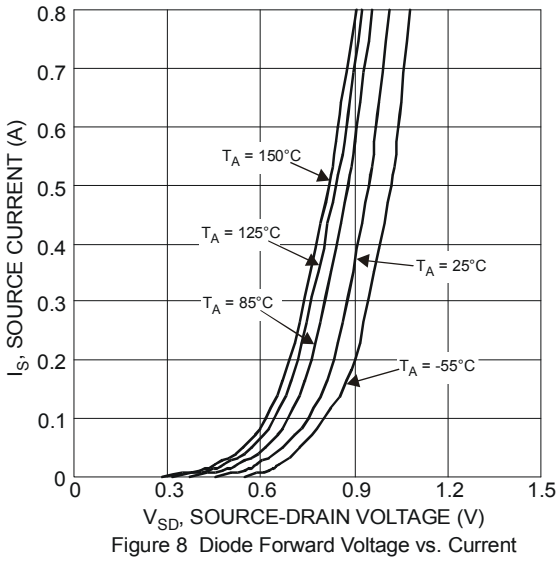



Figure 8 Diode Forward Voltage vs. Current

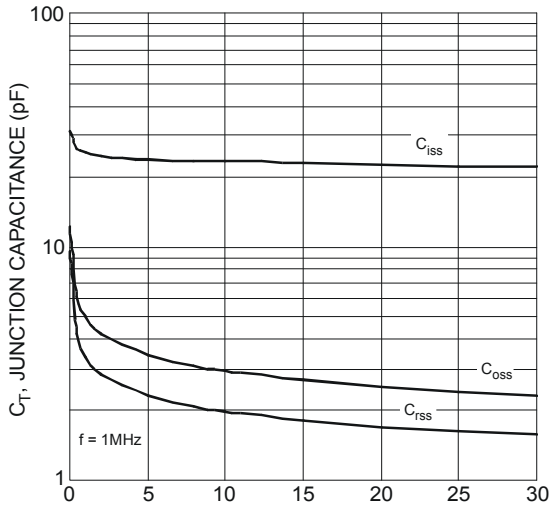



Figure 9 Typical Junction Capacitance

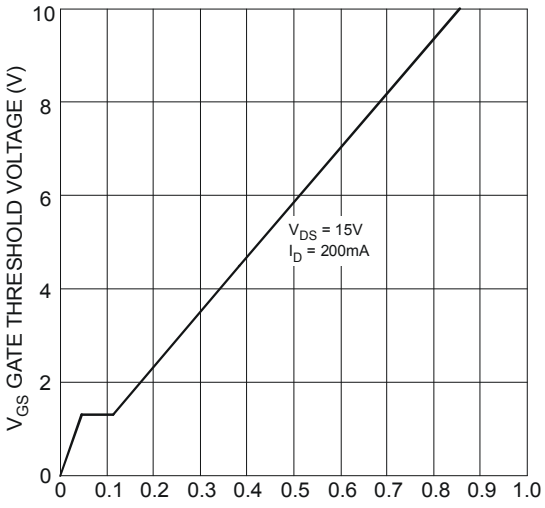



Figure 10 Gate Charge

NEW PRODUCT

## P-CHANNEL

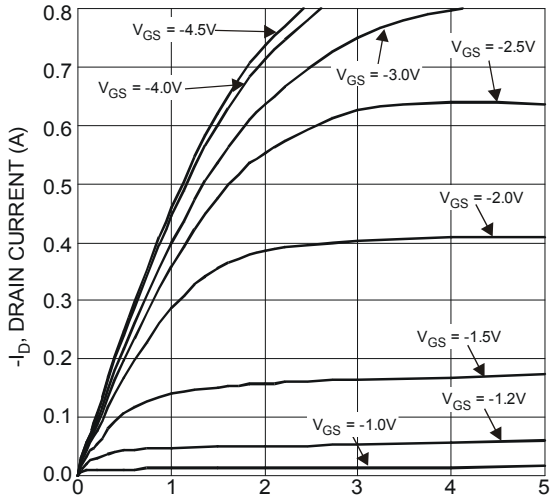



Figure 1 Typical Output Characteristics

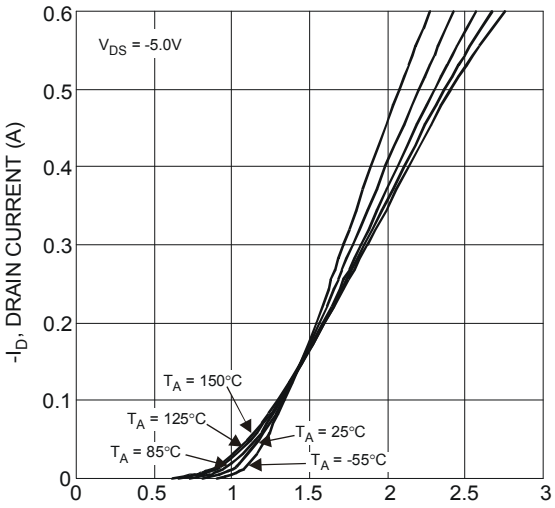



Figure 2 Typical Transfer Characteristics

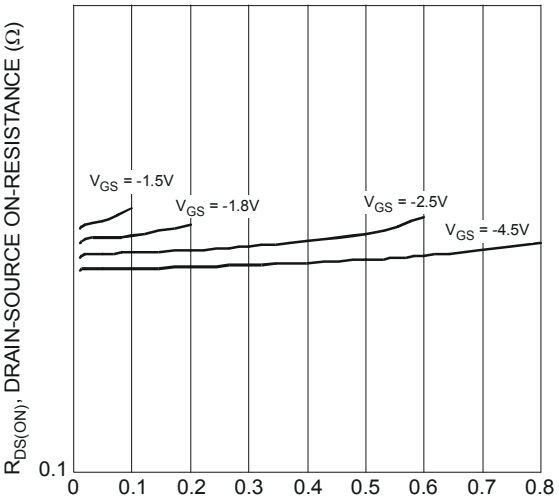



Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

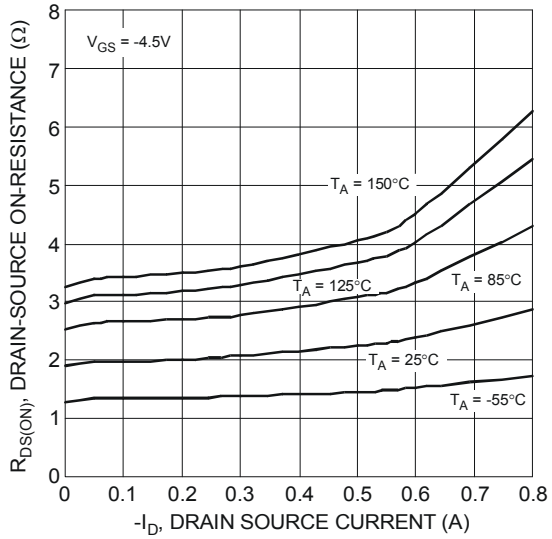



Figure 4 Typical On-Resistance vs. Drain Current and Temperature

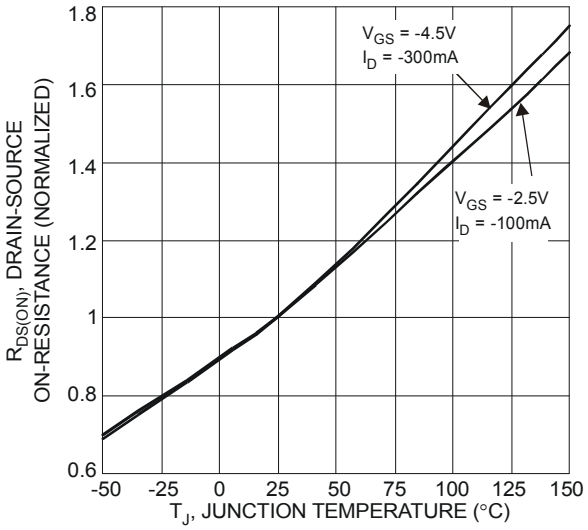



Figure 5 On-Resistance Variation with Temperature

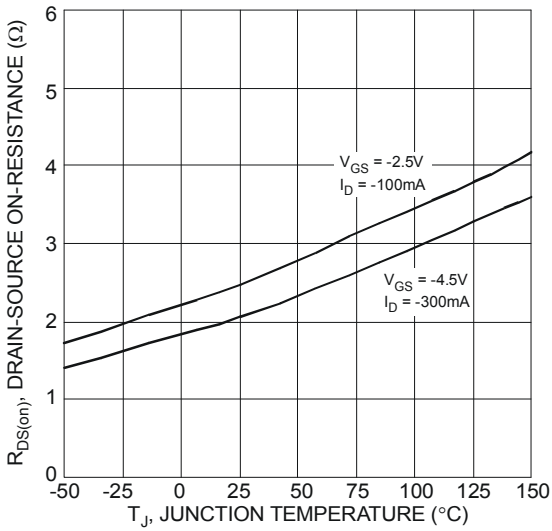



Figure 6 On-Resistance Variation with Temperature

NEW PRODUCT

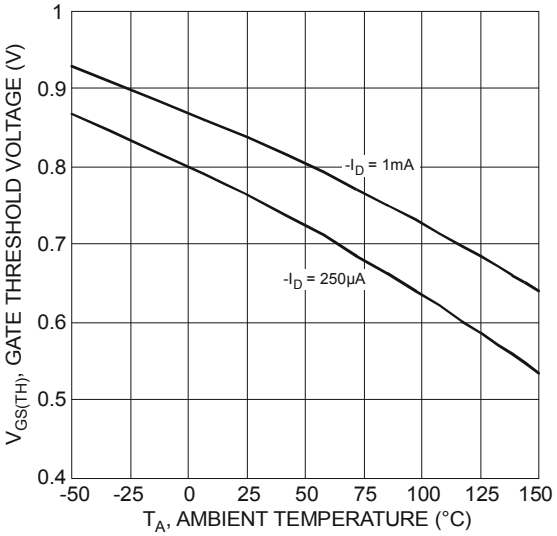



Figure 7 Gate Threshold Variation vs. Ambient Temperature

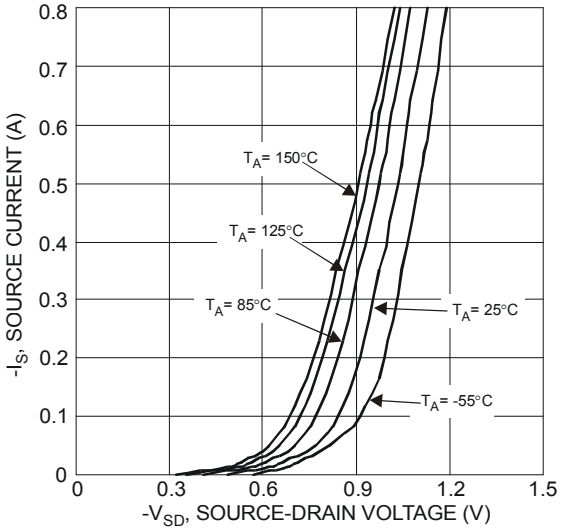



Figure 8 Diode Forward Voltage vs. Current

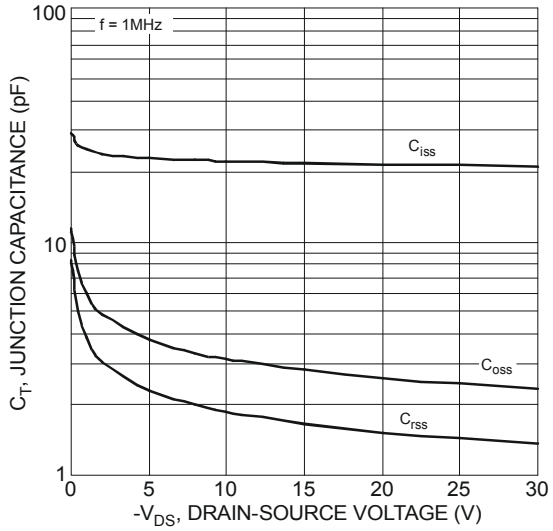



Figure 9 Typical Junction Capacitance

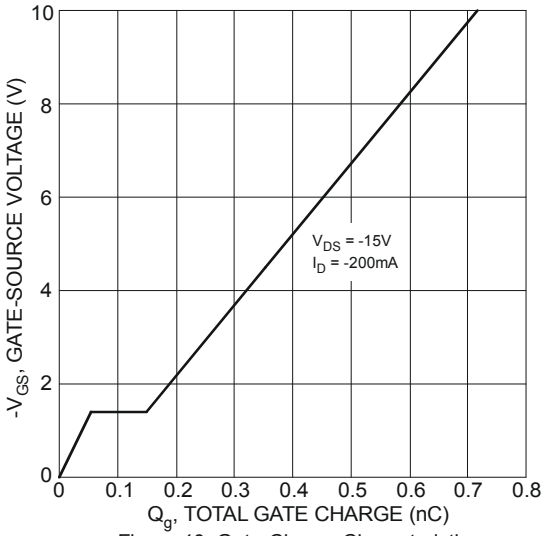



Figure 10 Gate-Charge Characteristics

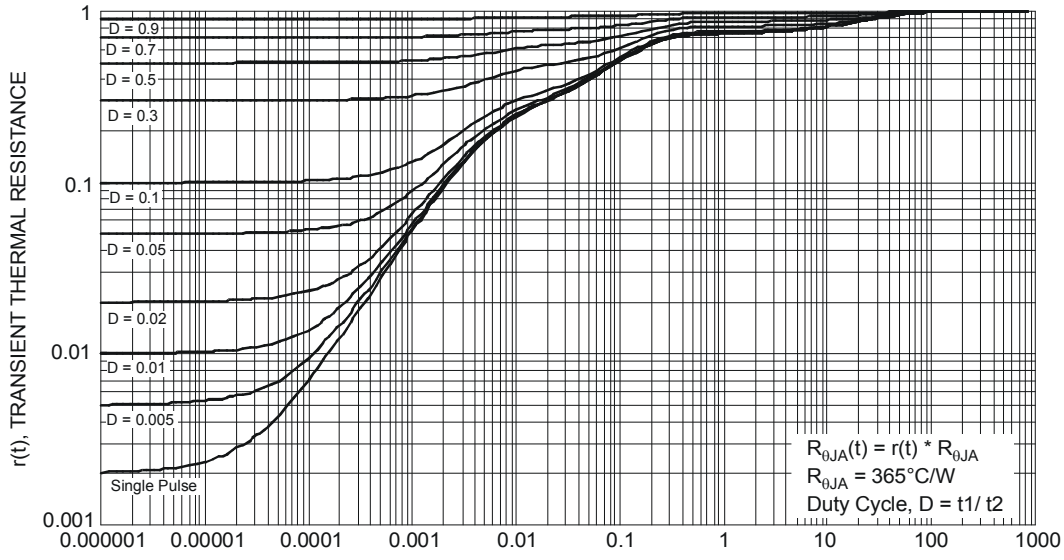
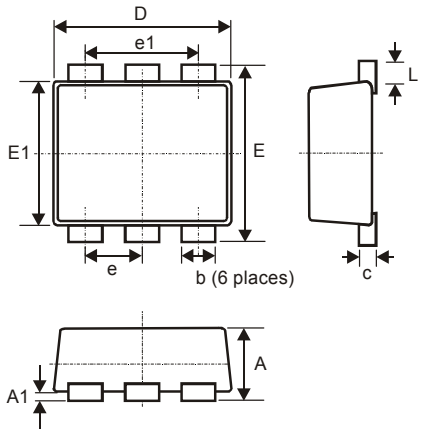



Figure 11 Transient Thermal Resistance

NEW PRODUCT

## Package Outline Dimensions

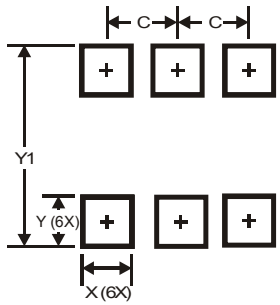
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.




| SOT963 | | | |
|---|---|---|---|
| Dim | Min | Max | Typ |
| A | 0.40 | 0.50 | 0.45 |
| A1 | 0 | 0.05 | - |
| c | 0.120 | 0.180 | 0.150 |
| D | 0.95 | 1.05 | 1.00 |
| E | 0.95 | 1.05 | 1.00 |
| E1 | 0.75 | 0.85 | 0.80 |
| L | 0.05 | 0.15 | 0.10 |
| b | 0.10 | 0.20 | 0.15 |
| e | 0.35 Typ | | |
| e1 | 0.70 Typ | | |
| All Dimensions in mm | | | |

## Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.




| Dimensions | Value (in mm) |
|---|---|
| C | 0.350 |
| X | 0.200 |
| Y | 0.200 |
| Y1 | 1.100 |

NEW PRODUCT

**IMPORTANT NOTICE**

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

**LIFE SUPPORT**

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

A. Life support devices or systems are devices or systems which:

1. are intended to implant into the body, or

2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.



**www.diodes.com**